162162

G00002

A B S T R A C T

A substrate processing method includes performing an etching process on a low dielectric constant film disposed on a substrate, thereby forming a predetermined pattern thereon; denaturing a remaining substance to be soluble in a predetermined liquid after the etching process; dissolving and removing the substance thus denatured, by supplying the predetermined liquid thereon; then, performing a silylation process on a surface of the low dielectric constant film, by supplying a silylation agent thereon, after said dissolving and removing the substance denatured; and baking the substrate after the silylation process.